N-Channel Logic Level MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY						
V _{DS} (V)	$r_{DS(on)}(\Omega)$	$I_{D}(A)$				
30	$0.027 @ V_{GS} = 10 V$	6.3				
30	$0.035 @ V_{GS} = 4.5V$	5.5				

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology





1	6
2	5
3	4

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Maximum	Units			
Drain-Source Voltage			30	V		
Gate-Source Voltage	V_{GS}	±20	V			
Continue Day in Comment	$T_A=25^{\circ}C$		6.3			
Continuous Drain Current ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$			A		
Pulsed Drain Current ^b	I_{DM}	±20				
Continuous Source Current (Diode Conduction) ^a	I_S	1.3	A			
D D: a	$T_A=25^{\circ}C$	D	1.6	W		
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	Ir D	1.0	**		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 5 sec	R_{THJA}	78.0	°C/W		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
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Parameter	Symbol	Symbol Test Conditions		Тур	Max	Unit	
Switch Off Characteristics							
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	$I_{ m DSS}$ -	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Current	-1022	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	u/ i	
Switch On Characteristics							
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1.0		3.0	V	
		$V_{GS} = 10 \text{ V}, I_D = 6.3 \text{ A}$			27		
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 6.3 \text{ A } T_J = 55^{\circ}\text{C}$			39	mΩ	
		$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$			35	1	
Forward Tranconductance ^A	g_{fs}	$V_{DS} = 10 \text{ V}, I_D = 6.3 \text{ A}$		45		S	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			A	
Diode Forward Voltage	V_{SD}	$I_S = 1.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V	
Dynamic ^b							
Total Gate Charge	Q_{g}	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 6.3 \text{ A}$		9		nC	
Gate-Source Charge	Q_{gs}	$v_{DS} = 13 \text{ v}, v_{GS} = 3 \text{ v}, I_D = 0.3 \text{ A}$ $R_L = 6 \Omega$		2.9			
Gate-Drain Charge	Q_{gd}	$K_L = 0.22$		3.2		1	
Switching Characteristics							
Turn-On Delay Time	$t_{d(on)}$			6			
Rise Time	t _r	$V_{DS} = 15 \text{ V}, R_L = 6 \Omega, I_D = 1 \text{ A},$		10			
Turn-Off Delay Time	$t_{ m d(off)}$	$V_{GEN} = 10 \text{ V}$		18		ns	
Fall-Time	t_{f}			5			

Notes

- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics (N-Channel)

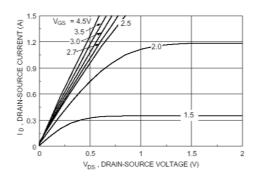


Figure 1. On-Region Characteristics

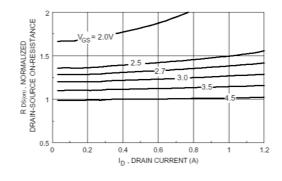


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

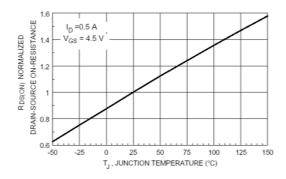


Figure 3. On-Resistance Variation with Temperature

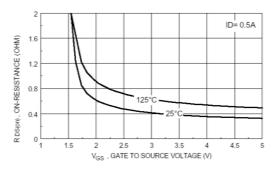


Figure 4. On-Resistance Variation with Gate to Source Voltage

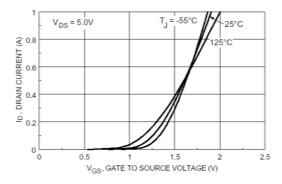


Figure 5. Transfer Characteristics

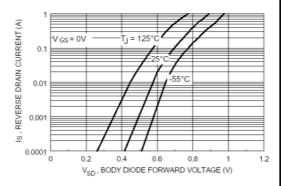


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics (N-Channel)

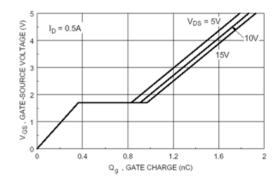


Figure 7. Gate Charge Characteristics.

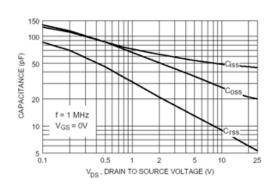


Figure 8. Capacitance Characteristics.

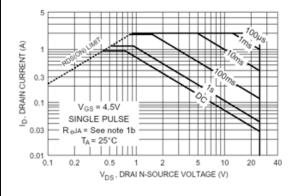


Figure 9. Maximum Safe Operating Area.

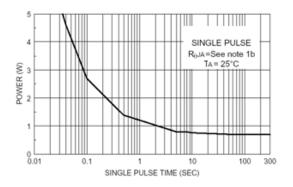


Figure 10. Single Pulse Maximum Power Dissipation.

Normalized Thermal Transient Junction to Ambient

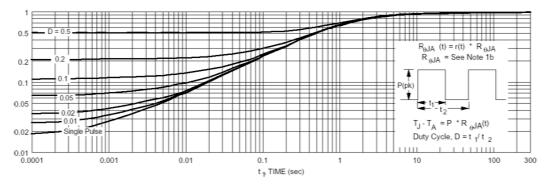
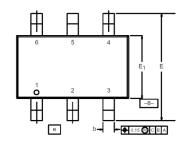
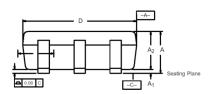


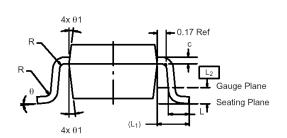
Figure 11. Transient Thermal Response Curve

Package Information

TSOP-6: 6LEAD







	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	_	1.10	0.036	_	0.043	
A ₁	0.01	_	0.10	0.0004	-	0.004	
A ₂	0.84	_	1.00	0.033	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е	1.00 BSC			0.0394 BSC			
L	0.35	_	0.50	0.014	_	0.020	
L ₁	0.60 Ref			0.024 Ref			
L ₂		0.25 BSC			0.010 BSC		
R	0.10	_	_	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ1	7° Nom			7° Nom			